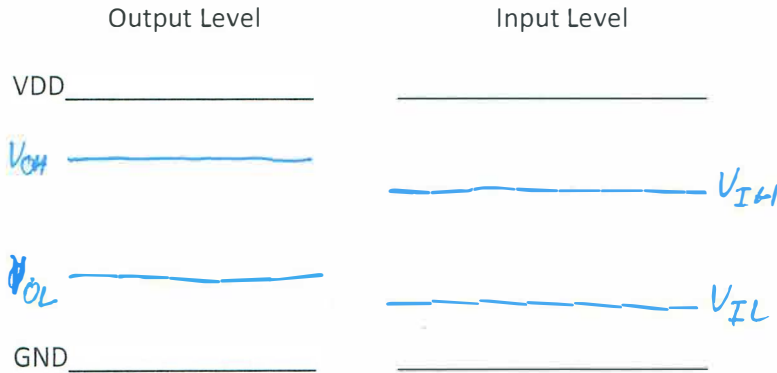


CE-1901-11 - Dr. Durant - Quiz 3
Winter 2016-'17, Week 3

1. (2 points) On the diagram below, **illustrate** values of V_{OH} , V_{IH} , V_{OL} , and V_{IL} that would allow logic 1 to be transmitted **correctly** but where logic 0 might **not be transmitted correctly** even when there is no noise.



$V_{IH} < V_{OH}$ has (positive) noise margin \rightarrow can tolerate some noise in logic!

$V_{IL} < V_{OL}$ is a problem. Transmitted V_{OL} (with noise) is received in unknown/forbidden region, $V_{IL} < x < V_{IH}$.

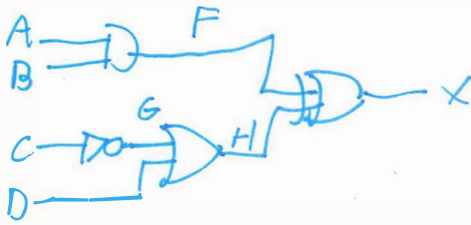
2. (2 points) **State and explain why either** a (relatively) positive or **negative** charge must be present at the gate of an PMOS transistor (specifically, a p-channel enhancement mode MOSFET [metal-oxide-semiconductor field-effect transistor]) in order for current to be **allowed to flow** between the drain and the source.

negative charge repels electrons from channel region

no, channel has electron vacancies in silicon lattice. These vacancies ("holes") are the specified (p = positive) charge carrier for a PMOS transistor, so current can flow between D & S.

3. (3 points) Draw the **gate diagram** for $X = (AB) \oplus (C' + D)$.

(3/4) NOR vs. XOR



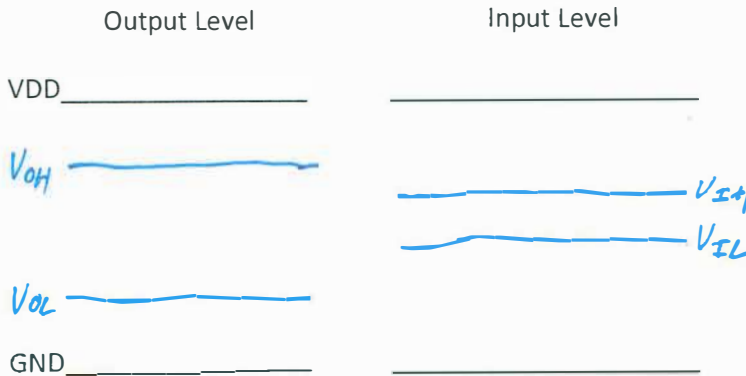
4. (3 points) **Complete** the truth table for the above function, including **all** intermediate terms. Be sure to clearly label all terms (some columns are labeled to get you started; you might not need all columns).

ABCD	$F = AB$	$G = \bar{C}$	$H = GD$	$H = G + D$		$X = F \oplus H$
0000	0	1	0	1		1
0001	0	1	1	1		1
0010	0	0	0	0		0
0011	0	0	0	1		1
0100	0	1	0	1		1
0101	0	1	1	1		1
0110	0	0	0	0		0
0111	0	0	0	1		1
1000	0	1	0	1		1
1001	0	1	1	1		1
1010	0	0	0	0		0
1011	0	0	0	1		1
1100	1	1	0	1		0
1101	1	1	1	1		0
1110	1	0	0	0		1
1111	1	0	0	1		0

↑
(-1/2) forgot this column, only

CE-1901-12 - Dr. Durant - Quiz 3
Winter 2016-'17, Week 3

1. (2 points) On the diagram below, **illustrate** values of V_{OH} , V_{IH} , V_{OL} , and V_{IL} that would enable proper operation.

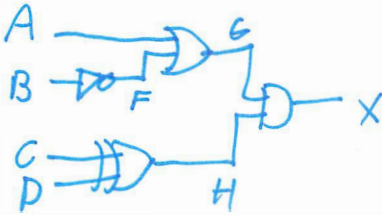


Must have: $V_{IH} < V_{OH}$
 $V_{IL} > V_{OL}$
to have (positive)
noise margin

2. (2 points) **State and explain why either** a (relatively) positive or negative charge must be present at the gate of an NMOS transistor (specifically, an n-channel enhancement mode MOSFET [metal-oxide-semiconductor field-effect transistor]) in order for current to be **blocked** ("cutoff") between the drain and the source.

- charge @ gate
repels electrons (e^-) from channel region
so, not enough carriers in channel to
conduct current

3. (3 points) Draw the **gate diagram** for $X = (A + B')(C \oplus D)$.



4. (3 points) **Complete** the truth table for the above function, including **all** intermediate terms. Be sure to clearly label all terms (some columns are labeled to get you started; you might not need all columns).

ABCD	$B' = F$	$G = A + F$	$H = C \oplus D$		$X = G \cdot H$
0000	1	1	0		0
0001	1	1	1		1
0010	1	1	1		1
0011	1	1	0		0
0100	0	0	0		0
0101	0	0	1		0
0110	0	0	1		0
0111	0	0	0		0
1000	1	1	0		0
1001	1	1	1		1
1010	1	1	1		1
1011	1	1	0		0
1100	0	1	0		0
1101	0	1	1		1
1110	0	1	1		1
1111	0	1	0		0